Atlas DCA

semiconductor component analyser

Model: DCA55



PRODUCT BRIEF

Features

• Connect any way round.

• Automatic component type identification.

Automatic pinout identification.

Transistor gain measurement.

 MOSFET gate threshold measurement.

 PN iunction characteristics measurements.

• Leakage current measurement.

Auto power on and power off.

• Ultra-slim and compact design.

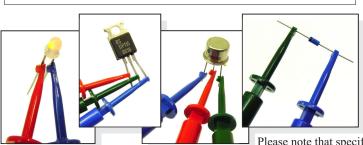
Supported Parts

• Transistors (Germanium and Silicon).

- Darlingtons.
- MOSFETs.
- Junction FETs (only gate pin identified).
- Low power thyristors and triacs.
- LEDs (including bicolour types).
- Diodes and diode networks.



Example Display for a typical transistor: NPN Silicon Here, the Atlas DCA has Transistor detected an NPN transistor. RED GREEN BLUE The pinout is then identified. Base Emit Coll Current gain DC current gain is measured FE=117 at a collector current of 2.5mA. est current =2.50mA Base-Emitter The Base-Emitter voltage E=0.71V drop is measured. est current IB=4.58mA eakage currer Finally, the collector leakage is measured.



Technical Specifications

| Parameter | Minimum | Typical | Maximum | Notes |
|---|--------------------|---------|-----------|-------|
| Peak test current into S/C | -5.5mA | | 5.5mA | 1 |
| Peak test voltage across O/C | -5.1V | | 5.1V | 1 |
| Measurable transistor gain range (H _{FE}) | 4 | | 65000 | 2 |
| Transistor gain accuracy (HFE<1000) | -3%-5 HFE | | +3%+5 HFE | 2,9 |
| Transistor V _{CEO} | 2.0V | | 3.0V | 2 |
| Transistor V _{BE} accuracy | -2%-20mV | | +2%+20mV | 9 |
| V _{BE} for Darlington identification | | 1.0V | | 3 |
| V _{BE} for Darlington identification (shunted) | | 0.8V | | 4 |
| Acceptable transistor V _{BE} | | | 1.80V | |
| Base-emitter shunt resistance threshold | | 60kΩ | | |
| Transistor collector-emitter test current | 2.45mA | 2.50mA | 2.55mA | |
| Acceptable transistor collector leakage | | 1.25mA | | 6 |
| MOSFET gate threshold range | 0.1V | | 5.0V | 5 |
| MOSFET gate threshold accuracy | -2%-20mV | | +2%+20mV | 5 |
| MOSFET drain-source test current | 2.45mA | 2.50mA | 2.55mA | |
| MOSFET minimum gate resistance | | 8kΩ | | |
| Thyristor/Triac gate test current | | 4.5mA | | 7 |
| Thyristor/Triac load test current | | 5.0mA | | |
| Diode test current | | | 5.0mA | |
| Diode forward voltage accuracy | -2%-20mV | | +2%+20mV | |
| V _F for LED identification | | 1.50V | | |
| Battery type | GP23A 12V Alkaline | | | |
| Battery voltage range | 7.50V | 12V | | |
| Battery voltage warning threshold | | 8.25V | | |
| Inactivity power-down period | | 30 secs | | |
| Dimensions (excluding test leads) | 103 x 70 x 20 mm | | | |
| Operating temperature range | 0°C | | 50°C | 8 |

- 1. Between any pair of test clips
- Collector current of 2.50mA. Resistance across reverse biased base-emitter $> 60 \text{k} \Omega$.
- 4. Resistance across reverse biased base-emitter < 60k Ω . 5. Drain-source current of 2.50mA.
- Collector-emitter voltage of 5.0V.
 Thyristor quadrant I, Triac quadrants I and III.
 Subject to acceptable LCD visibility.
- 9. BJT with no shunt resistors
- Please note that specifications of our products are subject to change without notice. E&OE. 02/08

Peak Electronic Design Limited

West Road House, West Road, Buxton, Derbyshire, SK17 6HF. Tel.+44 (0)1298 70012, Fax. +44 (0)1298 70046